



- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

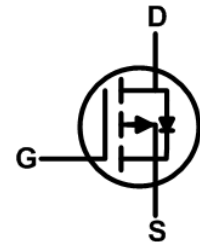
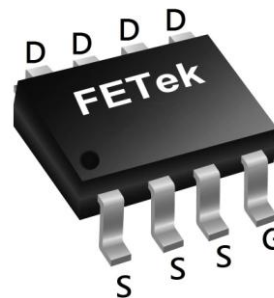
**Product Summary**

BVDSS	RDSON	ID
-30V	8.7mΩ	-14A

**Description**

The FKS3115 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The FKS3115 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

**SOP8 Pin Configuration****Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10\text{V}^1$	-14	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10\text{V}^1$	-11	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	-56	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	151	mJ
$I_{AS}$	Avalanche Current	-55	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation <sup>4</sup>	1.5	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup> ( $t \leq 10\text{s}$ )	---	40	$^\circ\text{C/W}$
	Thermal Resistance Junction-Ambient <sup>1</sup>	---	75	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	24	$^\circ\text{C/W}$



**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	-0.018	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-12A	---	---	8.7	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A	---	---	13.5	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.2	---	-2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	5.04	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	-5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-12A	---	25	---	S
Q <sub>g</sub>	Total Gate Charge (-4.5V)	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-12A	---	30	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	10	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	10.4	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-15V, V <sub>GS</sub> =-10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =-1A	---	9.4	---	ns
T <sub>r</sub>	Rise Time		---	10.2	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	117	---	
T <sub>f</sub>	Fall Time		---	24	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz	---	3448	---	pF
C <sub>oss</sub>	Output Capacitance		---	508	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	421	---	

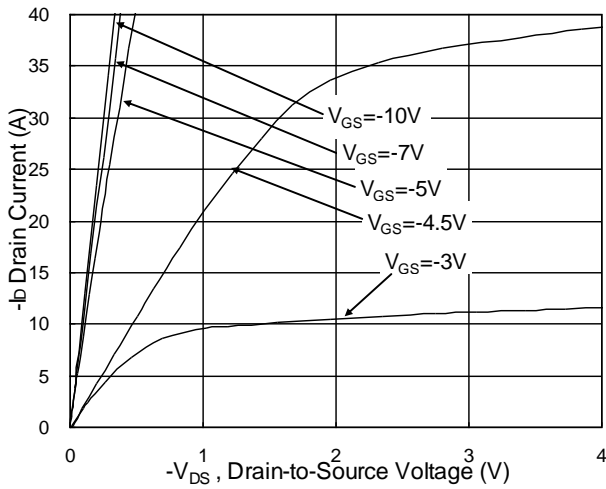
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-14	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,5</sup>		---	---	-56	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =-10A, di/dt=100A/μs,	---	19.4	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge	T <sub>J</sub> =25°C	---	9.1	---	nC

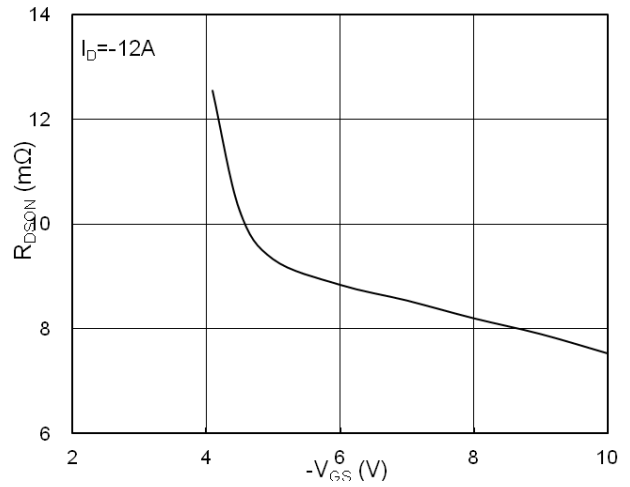
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=-25V, V<sub>GS</sub>=-10V, L=0.1mH, I<sub>AS</sub>=-55A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

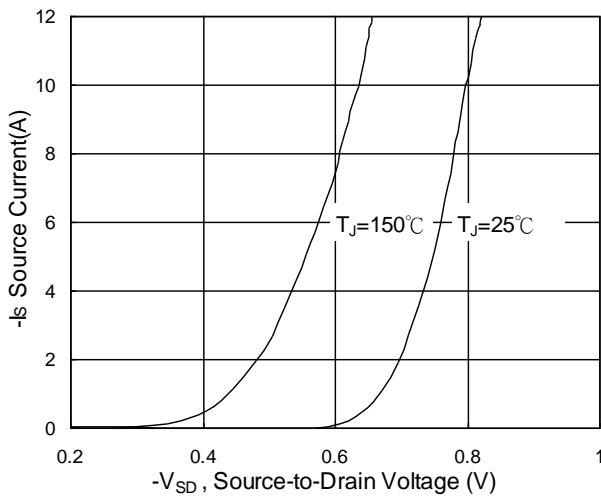
**Typical Characteristics**



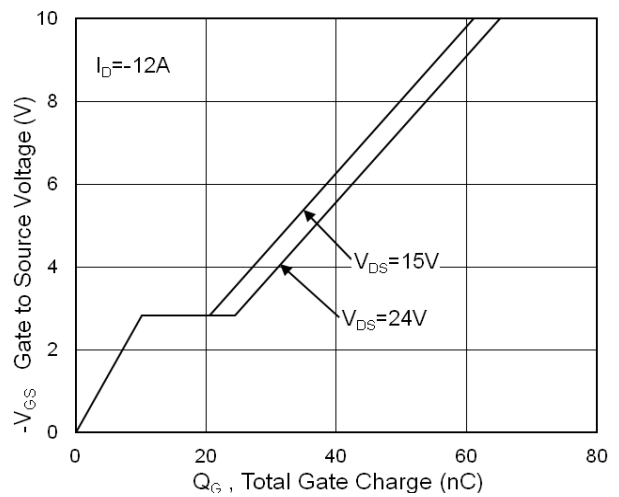
**Fig.1 Typical Output Characteristics**



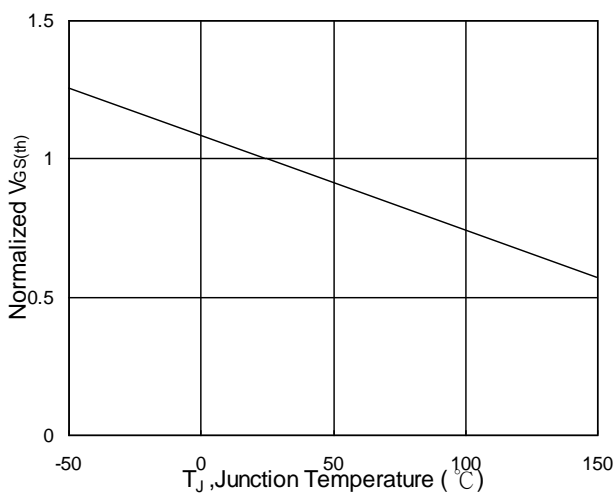
**Fig.2 On-Resistance v.s Gate-Source**



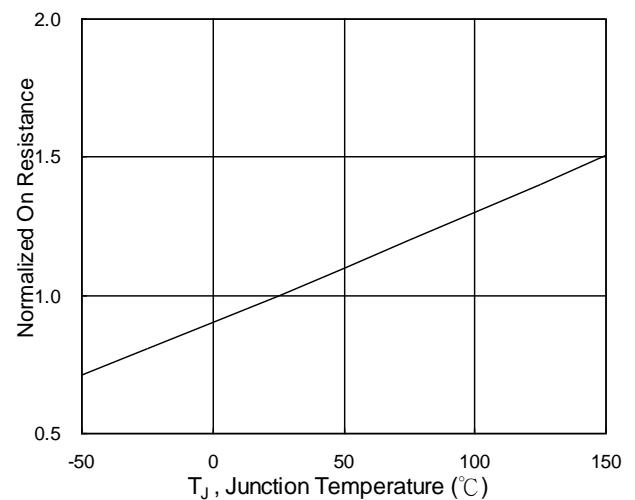
**Fig.3 Forward Characteristics Of Reverse**



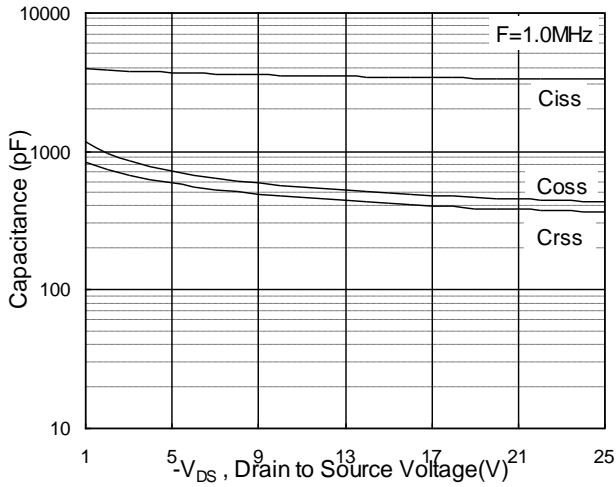
**Fig.4 Gate-Charge Characteristics**



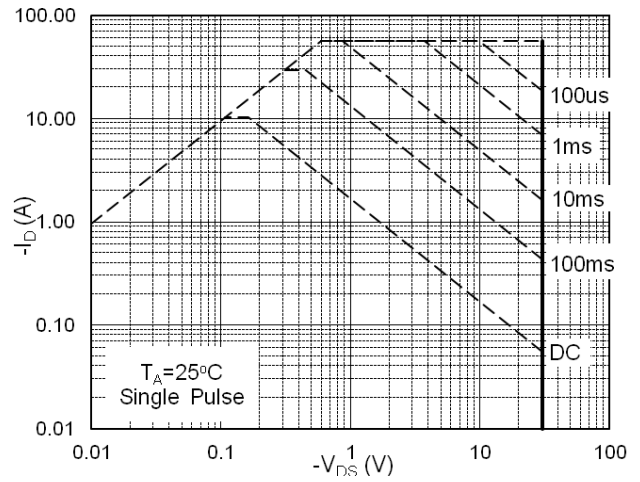
**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



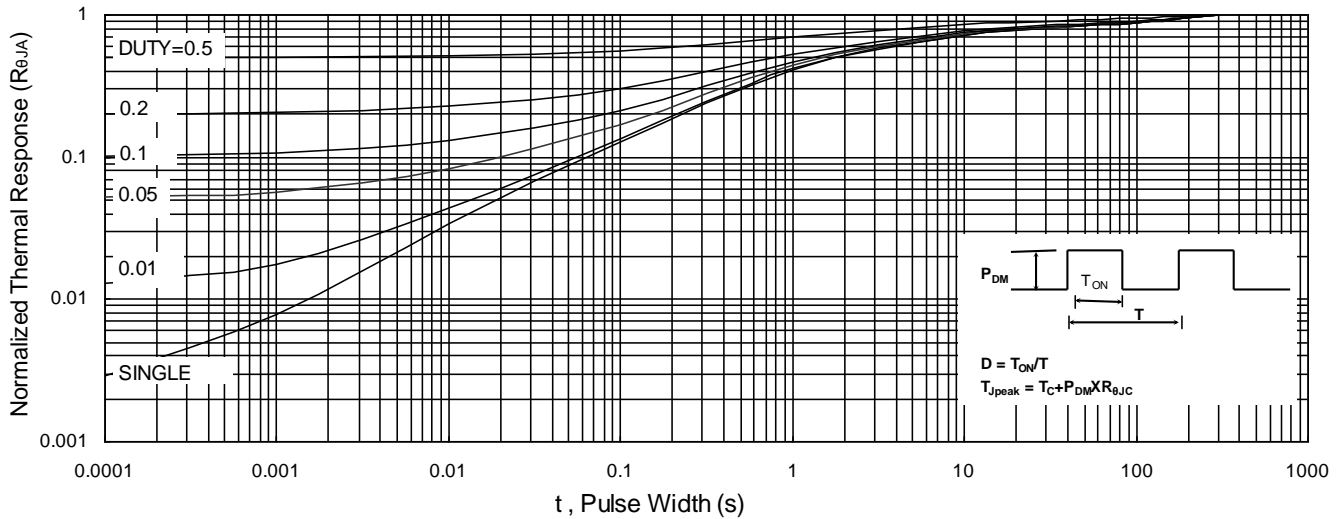
**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**



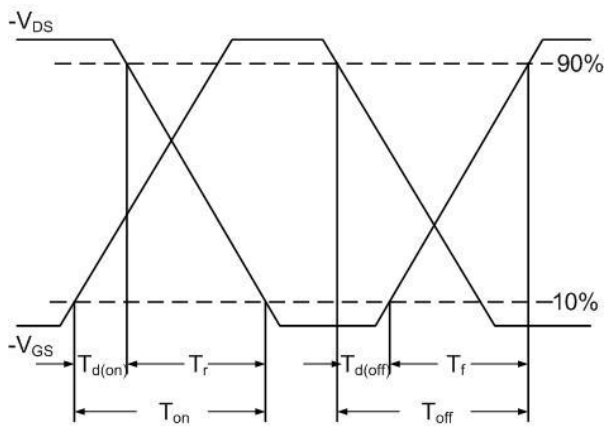
**Fig.7 Capacitance**



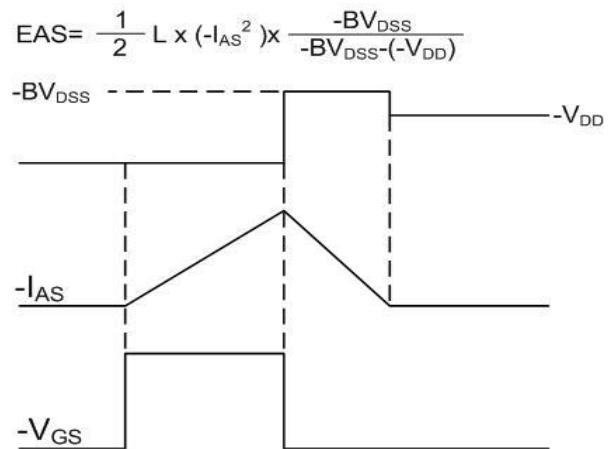
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Switching Waveform**